

In re Application of

Bojarczuk, et al.

Serial No.:

09/755,164

**Group Art Unit:** 

2826

Filed:

January 8, 2001

Examiner:

Quinto, Kevin V.

For:

ALUMINUM NITRIDE AND ALUMINUM OXIDE/ALUMINUM NITRIDE HETEROSTRUCTURE GATE DIELECTRIC STACK BASED FIELD EFFECT

TRANSISTORS AND METHOD FOR FORMING SAME

Honorable Commissioner of Patents Alexandria, VA 22313 - 1450

## AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated March 24, 2004, please amend the above-identified application as follows:

## **INTRODUCTORY COMMENTS**

Claims 1, 3, 7, 15-18, 28, and 30-31 are all the claims presently pending in the application. Claims 1, 3, 7, 15, 17, 28, and 30-31 have been amended to more clearly define the invention and claims 2, 4-6, 14, and 29 have been canceled. Claims 1, 15, and 17 are independent.